Elektronische Bauelemente

2N7002W

115 mAMPS, 60VOLTS, $R_{DS(on)}$=7.5

Small Signal MOSFET

RoHS Compliant Product

A suffix of "-C" specifies halogen & lead-free

N–Channel SOT–323

MAXIMUM RATINGS

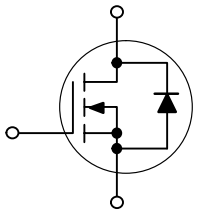
Rating	Symbol	Value	Unit
Drain–Source Voltage	V_{DSS}	60	Vdc
Drain–Gate Voltage (R_{GS} = 1.0 MΩ)	V_{DGR}	60	Vdc
Drain Current – Continuous T_C = 25°C (Note 1.) T_C = 100°C (Note 1.) – Pulsed (Note 2.)	I_D I_D I_{DM}	±115 ±75 ±800	mAdc
Gate–Source Voltage – Continuous – Non–repetitive ($t_p \leq 50$ μs)	V_{GS} V_{GSM}	±20 ±40	Vdc Vpk

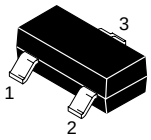
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 3.) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate,(Note 4.) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	°C

1. The Power Dissipation of the package may result in a lower continuous drain current.
2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
3. FR–5 = 1.0 x 0.75 x 0.062 in.
4. Alumina = 0.4 x 0.3 x 0.025 in 99.5% alumina.

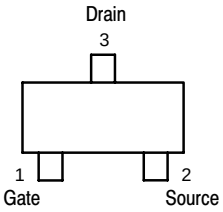
N–Channel





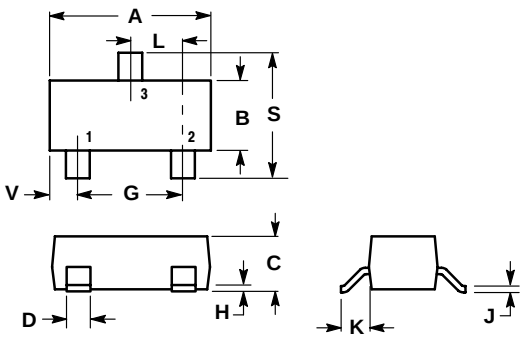
SOT–323

MARKING DIAGRAM & PIN ASSIGNMENT



K72 , 702 = Device Code

SOT-323		
Dim	**Min**	**Max**
A	1.800	2.200
B	1.150	1.350
C	0.800	1.000
D	0.300	0.400
G	1.200	1.400
H	0.000	0.100
J	0.100	0.250
K	0.350	0.500
L	0.590	0.720
S	2.000	2.400
V	0.280	0.420
All Dimension in mm		



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain–Source Breakdown Voltage (V_{GS} = 0, I_D = 10 μAdc)		$V_{(BR)DSS}$	60	–	–	Vdc
Zero Gate Voltage Drain Current (V_{GS} = 0, V_{DS} = 60 Vdc)	T_J = 25°C T_J = 125°C	I_{DSS}	– –	– –	1.0 500	μAdc
Gate–Body Leakage Current, Forward (V_{GS} = 20 Vdc)		I_{GSSF}	–	–	100	nAdc
Gate–Body Leakage Current, Reverse (V_{GS} = –20 Vdc)		I_{GSSR}	–	–	–100	nAdc
ON CHARACTERISTICS (Note 2.)						
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 250 μAdc)		$V_{GS(th)}$	1.0	–	2.5	Vdc
On–State Drain Current (V_{DS} ≥ 2.0 $V_{DS(on)}$, V_{GS} = 10 Vdc)		$I_{D(on)}$	500	–	–	mA
Static Drain–Source On–State Voltage (V_{GS} = 10 Vdc, I_D = 500 mAdc) (V_{GS} = 5.0 Vdc, I_D = 50 mAdc)		$V_{DS(on)}$	 – –	 – –	 3.75 0.375	Vdc
Static Drain–Source On–State Resistance (V_{GS} = 10 V, I_D = 500 mAdc) (V_{GS} = 5.0 Vdc, I_D = 50 mAdc) Forward Transconductance (V_{DS} ≥ 2.0 $V_{DS(on)}$, I_D = 200 mAdc)	T_C = 25°C T_C = 125°C T_C = 25°C T_C = 125°C	$r_{DS(on)}$ g_{FS}	 – – – – 80	 – – – – –	 7.5 13.5 7.5 13.5 –	Ohms mmhos
DYNAMIC CHARACTERISTICS						
Input Capacitance (V_{DS} = 25 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{iss}	–	–	50	pF
Output Capacitance (V_{DS} = 25 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{oss}	–	–	25	pF
Reverse Transfer Capacitance (V_{DS} = 25 Vdc, V_{GS} = 0, f = 1.0 MHz)		C_{rss}	–	–	5.0	pF
SWITCHING CHARACTERISTICS (Note 2.)						
Turn–On Delay Time	(V_{DD} = 25 Vdc, I_D ≅ 500 mAdc, R_G = 25 Ω, R_L = 50 Ω, V_{gen} = 10 V)	$t_{d(on)}$	–	–	20	ns
Turn–Off Delay Time		$t_{d(off)}$	–	–	40	ns
BODY–DRAIN DIODE RATINGS						
Diode Forward On–Voltage (I_S = 11.5 mAdc, V_{GS} = 0 V)		V_{SD}	–	–	–1.5	Vdc
Source Current Continuous (Body Diode)		I_S	–	–	–115	mAdc
Source Current Pulsed		I_{SM}	–	–	–800	mAdc

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

TYPICAL ELECTRICAL CHARACTERISTICS

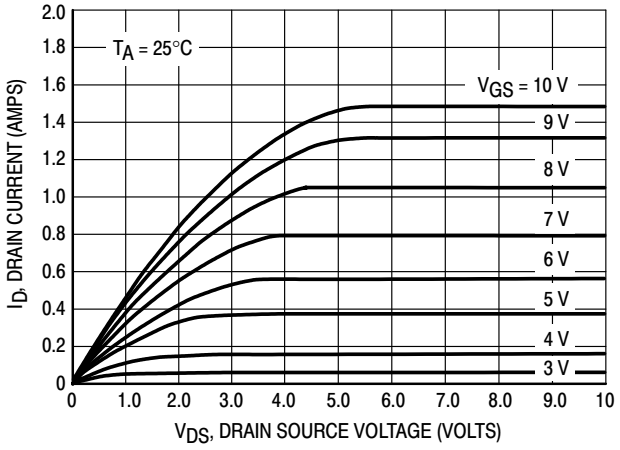


Figure 1. Ohmic Region

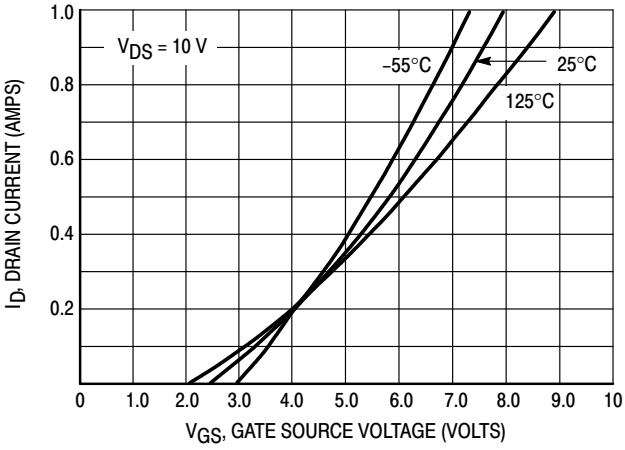


Figure 2. Transfer Characteristics

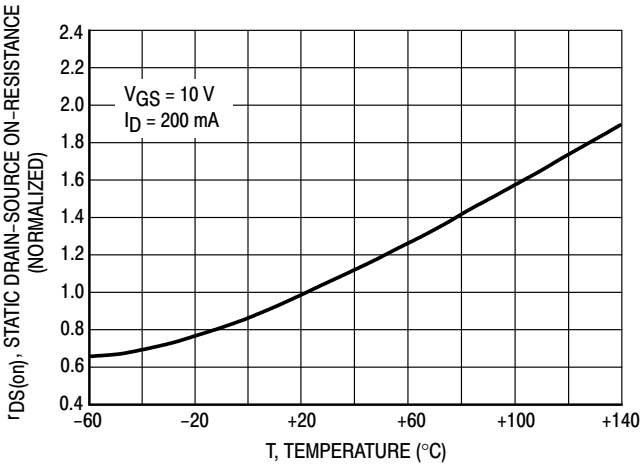


Figure 3. Temperature versus Static Drain–Source On–Resistance

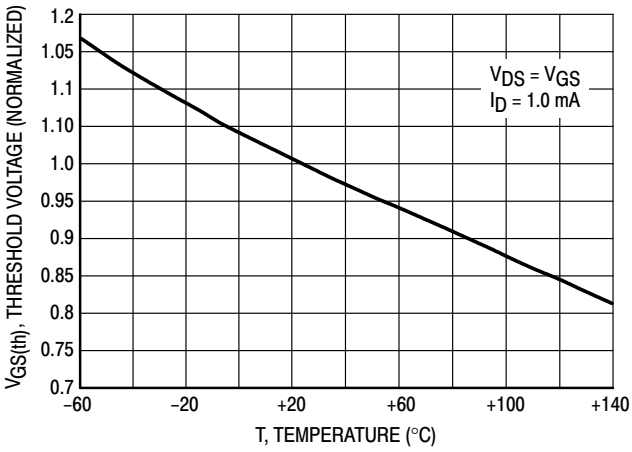


Figure 4. Temperature versus Gate Threshold Voltage